



Intel And Micron First To Deliver Sub-40 Nanometer NAND Flash Memory Device

May 29, 2008 at 12:00 AM EDT

Boise, Idaho and Santa Clara, California , Thursday, May 29, 2008 – Today Intel Corporation and Micron Technology, Inc. introduced the industry's first sub-40 nanometer (nm) NAND memory device, unveiling a 34nm 32 gigabit (Gb) multi-level cell chip. This process technology was jointly developed by Intel and Micron and manufactured by the companies' NAND flash joint venture, IM Flash Technologies (IMFT). It is the smallest NAND process geometry on the market. The 32 Gb NAND chip is the only monolithic device at this density that fits into a standard 48-lead thin small-outline package (TSOP), providing a cost-effective path to higher densities in existing applications. Shipments of customer samples begin in June and mass production is expected during the second half of this calendar year.

"This new 32 Gb device provides the best bit storage density available in the industry," said Brian Shirley, vice president of Micron's Memory Group. "Together with our partners at Intel, we're proud to have now taken the lead in production process technology."

"The introduction of 34nm process technology highlights IMFT's rapid progress and moves us to the forefront of NAND process technology," said Pete Hazen, director of marketing, Intel NAND Products Group. "These advancements will expand the value proposition and accelerate the adoption of solid-state drive (SSD) solutions in computing platforms."

The 34nm 32 Gb chips will be manufactured on 300 millimeter wafers, each producing approximately 1.6 terabytes of NAND. Measuring just 172mm², less than the size of a thumbnail, the 34nm 32 Gb chip will cost-effectively enable high-density solid-state storage in small form factor applications.

- A single 32 Gb chip could store more than 2,000 high-resolution digital photos or hold up to 1,000 songs on a personal music player.
- Two 8-die stacked packages would realize 64 gigabytes (GBs) of storage, enough for recording anywhere from eight to 40 hours of high-definition video in a digital camcorder.

The 34nm 32Gb chip was designed with solid-state drives in mind. The product will enable more cost-effective SSDs, instantly doubling the current storage volume of these devices and driving capacities to beyond 256 GBs in today's standard, smaller 1.8-inch form factor. SSDs are becoming the new storage medium for notebook computers, providing lower power, faster boot-up time, increased reliability, improved performance and reduced noise than hard disk drives. With the innovations in NAND process technology, such as with the 34nm NAND process, SSDs now offer a significant range of capacities to meet market requirements.

Based on the 34nm architecture, Intel and Micron also plan to introduce lower density multi-level cell products including single-level cell products, by the end of this calendar year.

About Intel

Intel (NASDAQ: INTC), the world leader in silicon innovation, develops technologies, products and initiatives to continually advance how people work and live. Additional information about Intel is available at www.intel.com/pressroom and <http://blogs.intel.com>. For more details on Intel NAND flash products go to www.intel.com/design/flash/nand.

About Micron

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets DRAMs, NAND flash memory, CMOS image sensors, other semiconductor components, and memory modules for use in leading-edge computing, consumer, networking, and mobile products. Micron's common stock is traded on the New York Stock Exchange (NYSE) under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

©2008 Micron Technology, Inc., and Intel Corporation. All rights reserved. Information is subject to change without notice.

Micron and the Micron logo are trademarks of Micron Technology, Inc. Intel is a trademark of Intel Corporation in the United States and other countries. All other trademarks are the property of their respective owners.

This press release contains forward-looking statements regarding the production of the 34nm 32 Gb NAND device. Actual events or results may differ materially from those contained in the forward-looking statements. Please refer to the documents the Company files on a consolidated basis from time to time with the Securities and Exchange Commission, specifically the Company's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for the Company on a consolidated basis to differ materially from those contained in our forward-looking statements (see Certain Factors). Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements.

Related Links

[Micron Media Center](#)

Contacts

Kirstin Bordner
Micron Technology, Inc.
208-368-5487
kbordner@micron.com

Connie Brown
Intel Corporation

503-264-4339

connie.m.brown@intel.com

Deborah Paquin

For Intel Corporation

916-984-1921

debpaquin@strategiccom.biz